

NTE2309 Silicon NPN Transistor High Voltage, High Current Switch

Features:

- High Breakdown Voltage
- Fast Switching Speed
- Wide ASO

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	900V
Collector–Emitter Voltage, V_{CEO}	800V
Emitter–Base Voltage, V_{EBO}	7V
Collector Current, I_C	
Continuous	12A
Peak (Note 1)	25A
Base Current, I_B	4A
Collector Dissipation ($T_A = +25^\circ\text{C}$), P_C	2.5W
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	100W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

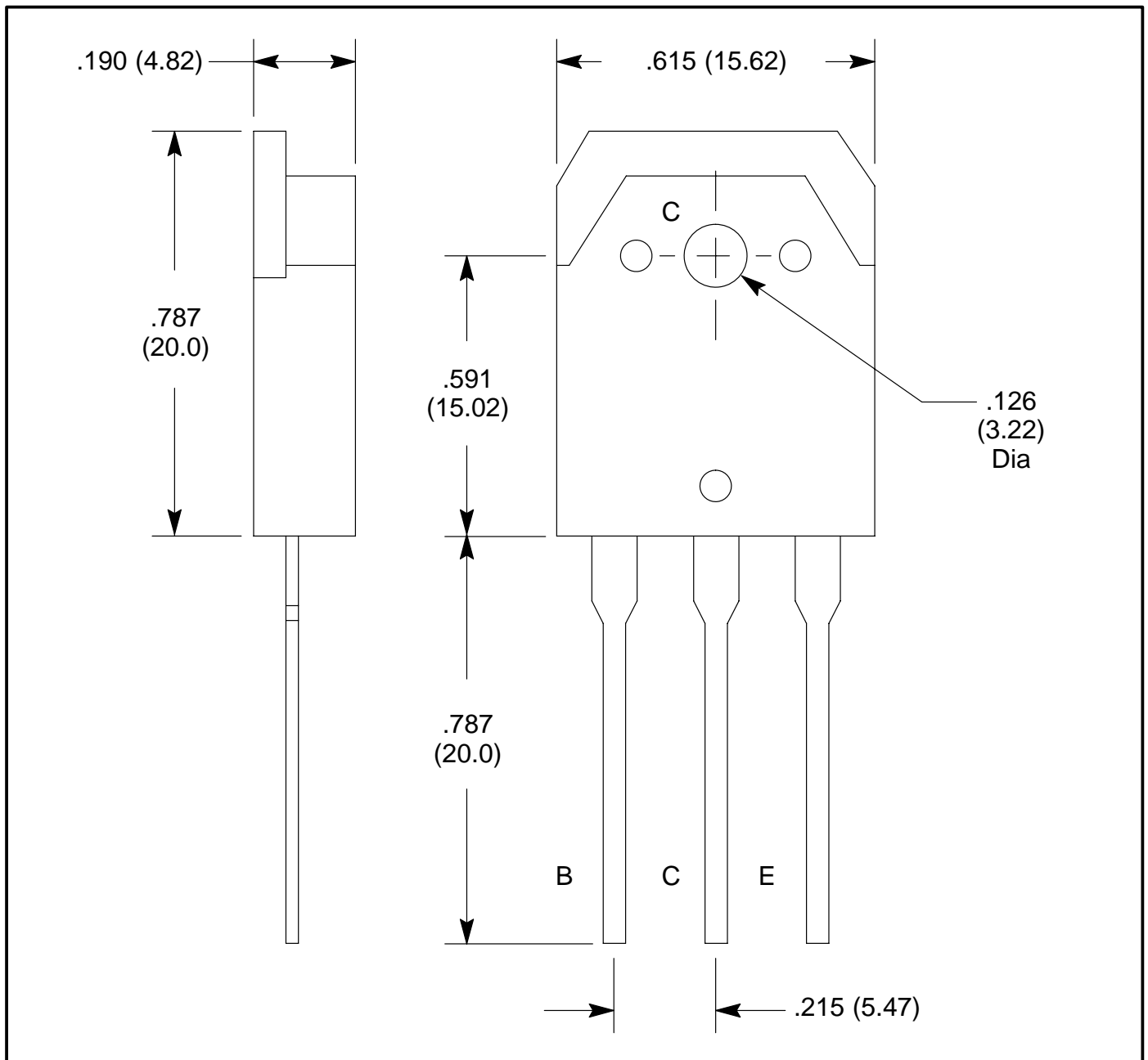
Note 1. Pules test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 10\%$.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 400\text{V}, I_E = 0$	–	–	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	–	–	10	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 0.4\text{A}$	10	–	–	
		$V_{CE} = 5\text{V}, I_C = 2\text{A}$	8	–	–	
Current Gain–Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 0.4\text{A}$	–	15	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3\text{A}, I_B = 0.6\text{A}$	–	–	2.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 3\text{A}, I_B = 0.6\text{A}$	–	–	1.5	V
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	–	120	–	pF

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}, I_E = 0$	900	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 5\text{mA}, R_{BE} = \infty$	800	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}, I_C = 0$	7	-	-	V
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 6\text{A}, I_B = 2\text{A}, L = 200\mu\text{H}$	800	-	-	V
	$V_{CEX(sus)}$	$I_C = 2\text{A}, I_{B1} = 0.4\text{A}, L = 1\text{mH}, I_{B2} = -0.4\text{A}, \text{Clamped}$	800	-	-	V
		$I_C = 1\text{A}, I_{B1} = 0.2\text{A}, L = 2\text{mH}, I_{B2} = -0.2\text{A}, \text{Clamped}$	900	-	-	V
Turn-On Time	t_{on}	$V_{CC} = 400\text{V}, I_C = 4\text{A}, I_{B1} = 0.8\text{A}, I_{B2} = -1.6\text{A}, R_L = 100\Omega$	-	-	1.0	μs
Storage Time	t_{stg}		-	-	3.0	μs
Fall Time	t_f		-	-	0.7	μs



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